**MMDT3904** 





### **40V DUAL NPN SMALL SIGNAL TRANSISTOR IN SOT363**

#### **Features**

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

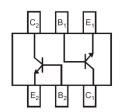
### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)

SOT363



Top View



Device Schematic Top View

## **Ordering Information** (Note 4)

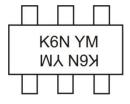
Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMDT3904-7-F	NRND	AEC-Q101	K6N	7	8	3,000
MMDT3904-7	Active	AEC-Q101	K6N	7	8	3,000

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS)\ \&\ 2011/65/EU\ (RoHS\ 2)\ compliant.$
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. NRND = Not Recommended for New Design. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

SOT363



 $\begin{array}{l} \mbox{K6N} = \mbox{Product Type Marking Code} \\ \mbox{YM} = \mbox{Date Code Marking} \\ \mbox{Y or } \overline{\mbox{Y}} = \mbox{Year (ex: A = 2013)} \\ \mbox{M or } \overline{\mbox{M}} = \mbox{Month (ex: 9 = September)} \\ \end{array}$ 

Date Code Key

Year	2013		2014	2015		2016	2017		2018	2019		2020
Code	Α		В	С		D	Е		F	G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	200	mA

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

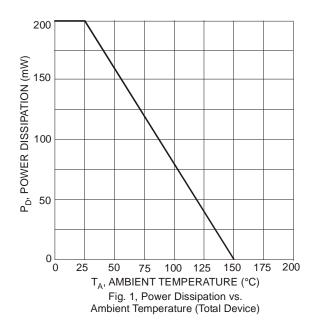
Notes:

<sup>5.</sup> For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristic and Derating Information**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$BV_{CBO}$	60		V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	$BV_{CEO}$	40	_	V	$I_C = 10.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0		V	$I_E = 100 \mu A, I_C = 0$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	50	nA	V <sub>CB</sub> = 50V
Collector-Emitter Cut-Off Current			50	nA	$V_{CE} = 40V, V_{BE(OFF)} = 3.0V$
Collector-Emitter Cut-On Current	I <sub>CEV</sub>		50	IIA	$V_{CE} = 40V, V_{BE(ON)} = 0.25V$
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	_	50	nA	V <sub>EB</sub> = 5V
ON CHARACTERISTICS (Note 7)					
		40	_		$I_C = 100\mu A$ , $V_{CE} = 1.0V$
		70	_		$I_C = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	300		$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$
		60	_		$I_C = 50 \text{mA}, V_{CE} = 1.0 \text{V}$
		30	_		$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$
Collector-Emitter Saturation Voltage	Vor.		0.20	V	$I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$
Conector-Enniter Saturation Voltage	V <sub>CE(sat)</sub>		0.30	V	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.65	0.85	V	$I_C = 10mA, I_B = 1.0mA$
ů		_	0.95	•	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS				ı	_
Output Capacitance	$C_{obo}$	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	1.0	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0V$ , $I_{C} = 100\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$
SWITCHING CHARACTERISTICS				1	1
Delay Time	t <sub>d</sub>	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	tr	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	t <sub>s</sub>	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t <sub>f</sub>	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Note:

<sup>7.</sup> Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

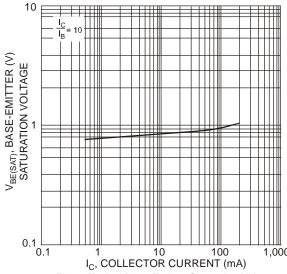
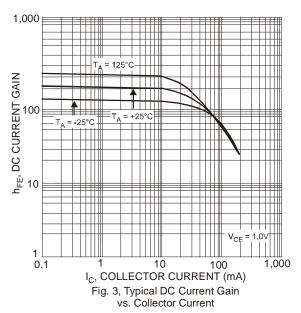
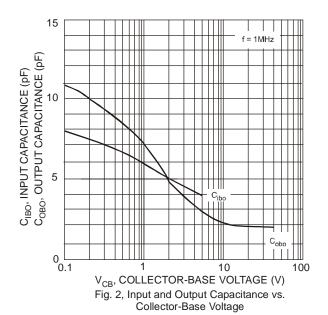


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current





VOLECTOR-EMITTER (V)

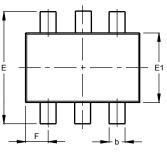
O'CE(SAT), COLLECTOR-EMITTER (V)

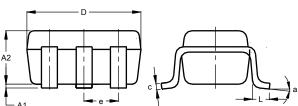
O'CE(SAT)



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

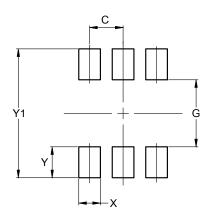




SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
E	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	(	).650 B	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а		8°				
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



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